



# PNP -10A -20V Middle Power Transistor

Parameter	Value
$V_{CEO}$	-20V
I <sub>C</sub>	-10A

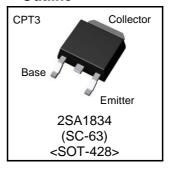
#### Features

- 1) Suitable for Middle Power Driver
- 2) Complementary NPN Types: 2SC5001
- 3) Low V<sub>CE(sat)</sub>

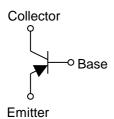
$$V_{CE(sat)} = -0.25V(Max.)$$
  
 $(I_C/I_B = -4A/-0.05A)$ 

- 4) Large collector current :  $I_C = -10A$  (DC Max.)
- 5) Lead Free/RoHS Compliant.

#### Outline



### •Inner circuit



## Applications

Motor driver, LED driver Power supply, strobe

## Packaging specifications

Part No.	Package	Package size (mm)	Taping code	Reel size (mm)	Tape width (mm)	Basic ordering unit (pcs)	Marking
2SA1834	CPT3	6595	TL	330	16	2,500	A1834

# ● Absolute maximum ratings (Ta = 25°C)

Parameter		Symbol	Values	Unit
Collector-base voltage		V <sub>CBO</sub>	-30	V
Collector-emitter voltage		V <sub>CEO</sub>	-20	V
Emitter-base voltage		$V_{EBO}$	-6	V
Collector current	DC	I <sub>C</sub>	-10	Α
	Pulsed	I <sub>CP</sub> *1	<b>−15</b>	Α
Power dissipation		P <sub>D</sub> *2	1	W
		P <sub>D</sub> *3	10	W
Junction temperature		T <sub>j</sub>	150	°C
Range of storage temperature		T <sub>stg</sub>	−55 to +150	°C

<sup>\*1</sup> Pw=10ms, single pulse

# ●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Collector-emitter breakdown voltage	BV <sub>CEO</sub>	$I_C = -1 \text{mA}$	-20	-	-	V
Collector-base breakdown voltage	BV <sub>CBO</sub>	$I_{C} = -50 \mu A$	-30	-	-	V
Emitter-base breakdown voltage	BV <sub>EBO</sub>	I <sub>E</sub> = -50μA	<b>–6</b>	ı	ı	V
Collector cut-off current	I <sub>CBO</sub>	$V_{CB} = -20V$	-	1	-1	μΑ
Emitter cut-off current	I <sub>EBO</sub>	$V_{EB} = -5V$	-	-	<b>–1</b>	μΑ
Collector-emitter saturation voltage	V <sub>CE(sat)</sub> *4	$I_C = -4A, I_B = -0.05A$	ı	-0.16	-0.25	٧
Base-emitter saturation voltage	V <sub>BE(sat)</sub> *4	$I_C = -4A, I_B = -0.05A$	ı	-0.9	-1.2	V
DC gurrent goin	h <sub>FE</sub> 1 *4	$V_{CE} = -2V, I_{C} = -0.5A$	180	ı	560	-
DC current gain	h <sub>FE</sub> 2 *4	$V_{CE} = -2V, I_{C} = -4A$	82	-	-	-
Transition frequency	$f_T^{^{*4}}$	$V_{CE} = -5V, I_{E} = 1.5A$ f=50MH <sub>Z</sub>	ı	150	ı	MHz
Output capacitance	$C_ob$	$V_{CB} = -10V$ , $I_E = 0A$ f = 1MHz	-	220	-	pF

<sup>\*4</sup> Pulsed

# $\bullet h_{\text{FE}} \ rank \ categories$

Rank	R	S
h <sub>FE</sub>	180 to 390	270 to 560

<sup>\*2</sup> Mounted on a substrate

<sup>\*3</sup> Tc=25°C

## ●Electrical characteristic curves(Ta = 25°C)

Fig.1 Ground Emitter Propagation Characteristics

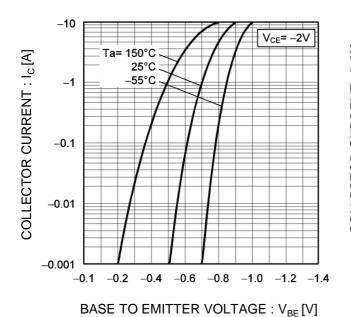
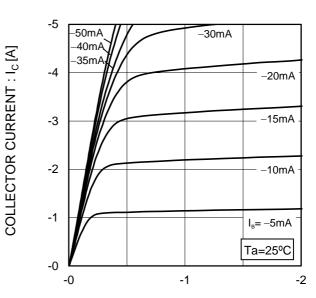


Fig.2 Typical Output Characteristics



COLECTOR TO EMITTE VOLTAGE :  $V_{CE}[V]$ 

Fig.3 DC Current Gain vs. Collector Current(I)

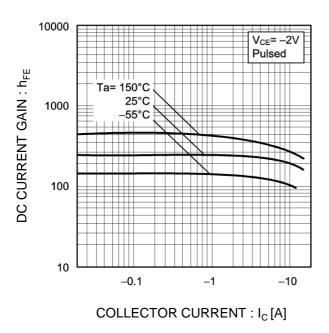
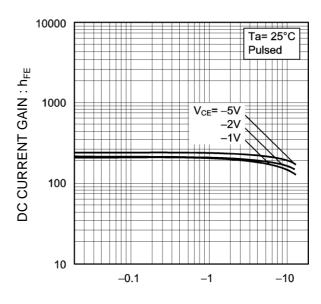


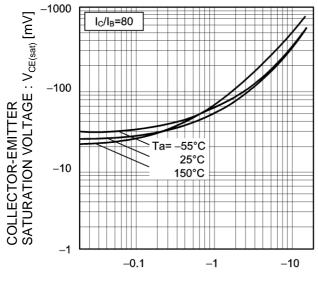
Fig.4 DC current gain vs. output current (II)



COLLECTOR CURRENT : I<sub>C</sub>[A]

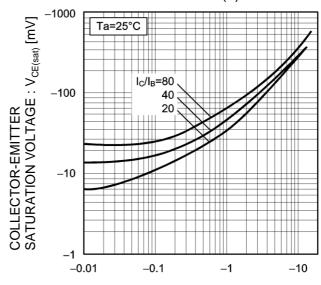
#### ●Electrical characteristic curves(Ta = 25°C)

Fig.5 Collector-Emitter Saturation Voltage vs. Collector Current (I)



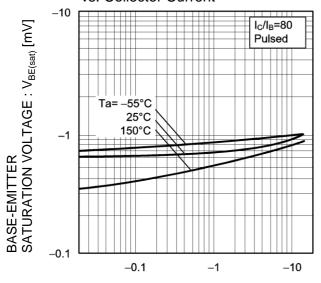
COLLECTOR CURRENT : I<sub>C</sub>[A]

Fig.6 Collector-Emitter Saturation Voltage vs. Collector Current (II)



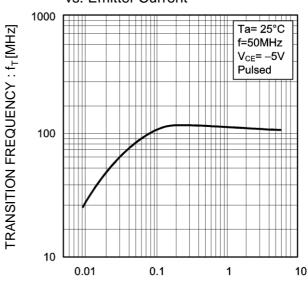
COLLECTOR CURRENT : I<sub>C</sub>[A]

Fig.7 Base-Emitter Saturation Voltage vs. Collector Current



COLLECTOR CURRENT :  $I_C[A]$ 

Fig.8 Gain Bandwidth Product vs. Emitter Current



 $\mathsf{EMITTER}\;\mathsf{CURRENT}: \mathsf{I}_\mathsf{E}\left[\mathsf{A}\right]$ 

# ●Electrical characteristic curves(Ta = 25°C)

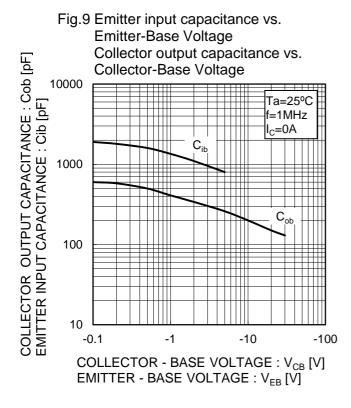
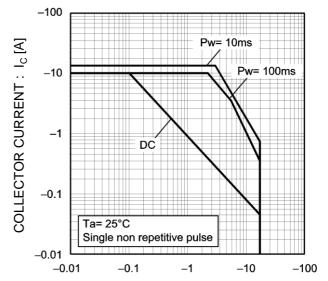
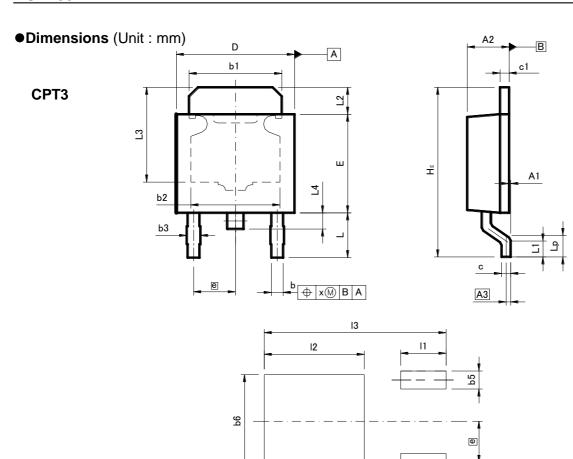


Fig.10 Safe Operating Area



COLLECTOR TO EMITTER VOLTAGE :  $V_{CE}\left[V\right]$ 



Pattern of terminal position areas [Not a recommended pattern of soldering pads]

DIM MILIMETERS		MILIMETERS INCHES			
DIM	MIN	MAX	MIN	MAX	
A1	0.00	0.15	0.000	0.006	
A2	2.20	2.50	0.087	0.098	
A3	0.2	25	0.010		
b	0.55	0.75	0.022	0.030	
b1	5.00	5.30	0.197	0.209	
b2	5.0		0.1	97	
b3	0.	75	0.0	30	
С	0.40	0.60	0.016	0.024	
c1	0.40	0.60	0.016	0.024	
D	6.30	6.70	0.248	0.264	
E	5.40	5.80	0.213	0.228	
е	2.3	30	0.091		
HE	9.00	10.00	0.354	0.394	
L	2.20	2.80	0.087	0.110	
L1	0.80	1.40	0.031	0.055	
L2	1.20	1.80	0.047	0.071	
L3	5.30		0.209		
L4	0.90		0.035		
Lp	1.00	1.60	0.039	0.063	
Х	_	0.25	_	0.010	

DIM	MILIM	ETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
b5	_	1.00	-	0.04	
b6	_	5.20	-	0.205	
l1	_	2.50	_	0.098	
12	_	5.50	-	0.217	
13	-	10.00	-	0.394	

Dimension in mm / inches

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